



2N6285 – 2N6286 – 2N6287

PNP DARLINGTON POWER SILICON TRANSISTOR

The 2N6285, 2N6286 and 2N6287 are mounted in TO-3 metal package. They are designed for use in general-purpose amplifier and low-frequency switching applications.

The complementary NPN are 2N6282, 2N6283, 2N6284
Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit
V_{CEO}	Collector-Emitter Voltage ($I_B=0$)	2N6285	-60	V
		2N6286	-80	
		2N6287	-100	
V_{CBO}	Collector-Base Voltage ($I_E=0$)	2N6285	-60	V
		2N6286	-80	
		2N6287	-100	
V_{EBO}	Emitter-Base Voltage ($I_C=0$)	2N6285	-5	V
		2N6286		
		2N6287		
I_C	Collector Current	2N6285	-20	A
		2N6286		
		2N6287		
I_{CM}	Collector Peak Current	2N6285	-40	A
		2N6286		
		2N6287		
I_B	Base Current	2N6285	-0.5	A
		2N6286		
		2N6287		
P_T	Power Dissipation	@ $T_C = 25^\circ$	160	W/°C
		2N6285		
		2N6286		
T_J	Junction Temperature	2N6285	200	°C
		2N6286		
		2N6287		
T_S	Storage Temperature	2N6285	-65 to +200	°C
		2N6286		
		2N6287		

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THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJ-C}	Thermal Resistance Junction-Case	1.09	°C/W

ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit	
$V_{CEO(SUS)}$	Collector-Emitter Breakdown Voltage (*)	$I_C = -200 \text{ mA}$ $I_B = 0$	2N6285	-60	-	-	V
			2N6286	-80	-	-	
			2N6287	-100	-	-	
I_{CEO}	Collector Cutoff Current	$V_{CE} = -30 \text{ V}, I_B = 0$	2N6285	-	-	-1	mA
		$V_{CE} = -40 \text{ V}, I_B = 0$	2N6286				
		$V_{CE} = -50 \text{ V}, I_B = 0$	2N6287				
I_{EBO}	Emitter Cutoff Current	$V_{BE} = -5 \text{ V}, I_C = 0$	2N6285	-	-	-2	mA
			2N6286				
			2N6287				
I_{CEX}	Collector Cutoff Current	$V_{CE} = -60 \text{ V}, V_{BE} = 1.5 \text{ V}$	2N6285	-	-	-500	μA
		$V_{CE} = -80 \text{ V}, V_{BE} = 1.5 \text{ V}$	2N6286				
		$V_{CE} = -100 \text{ V}, V_{BE} = 1.5 \text{ V}$	2N6287				
		$V_{CE} = 60 \text{ V}, V_{BE} = 1.5 \text{ V}$ $T_C = 150^\circ\text{C}$	2N6285	-	-	-5	mA
		$V_{CE} = -80 \text{ V}, V_{BE} = 1.5 \text{ V}$ $T_C = 150^\circ\text{C}$	2N6286				
		$V_{CE} = -100 \text{ V}, V_{BE} = 1.5 \text{ V}$ $T_C = 150^\circ\text{C}$	2N6287				
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C = -10 \text{ A}, I_B = -40 \text{ mA}$	2N6285	-	-	-2	V
			2N6286				
			2N6287				
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C = -20 \text{ A}, I_B = -200 \text{ mA}$	2N6285	-	-	-3	V
			2N6286				
			2N6287				
$V_{BE(SAT)}$	Base-Emitter saturation Voltage (*)	$I_C = -20 \text{ A}, I_B = -200 \text{ mA}$	2N6285	-	-	-4	V
			2N6286				
			2N6287				
V_{BE}	Base-Emitter Voltage (*)	$V_{CE} = -3 \text{ V}, I_C = -10 \text{ A}$	2N6285	-	-	-2,8	V
			2N6286				
			2N6287				

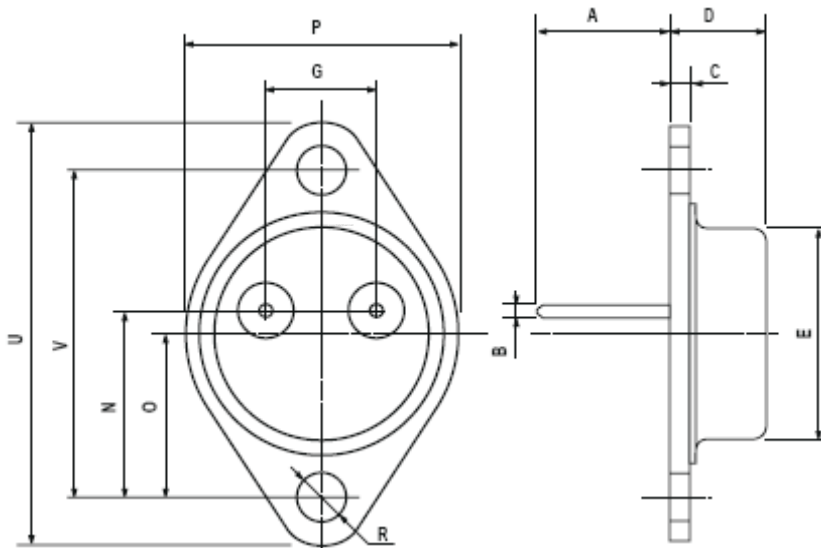
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Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit	
h_{FE}	DC Current Gain (*)	$V_{CE} = -3\text{ V}, I_C = -10\text{ A}$	2N6285	750	-	18000	-
			2N6286				
			2N6287				
		$V_{CE} = -3\text{ V}, I_C = -20\text{ A}$	2N6285	100	-	-	
			2N6286				
			2N6287				
C_{OB}	Output Capacitance	$I_E = 0\text{ A}, V_{CB} = -10\text{ V}$ $f = 1\text{ MHz}$	2N6285	-	-	400	pF
			2N6286				
			2N6287				

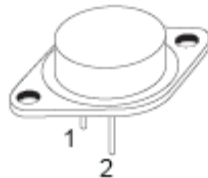
(*) Pulse Width $\approx 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$

MECHANICAL DATA CASE TO-3

DIMENSIONS (mm)		
	min	max
A	11	13.10
B	0.97	1.15
C	1.5	1.65
D	8.32	8.92
F	19	20
G	10.70	11.1
N	16.50	17.20
P	25	26
R	4	4.09
U	38.50	39.30
V	30	30.30



Pin 1 :	Base
Pin 2 :	Emitter
Case :	Collector



Revised August 2012

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